

## SNx4HC00 Quadruple 2-Input NAND Gates

### 1 Features

- Buffered inputs
- Wide operating voltage range: 2 V to 6 V
- Wide operating temperature range: –40°C to +85°C
- Supports fanout up to 10 LSTTL loads
- Significant power reduction compared to LSTTL logic ICs

### 2 Applications

- [Alarm / tamper detect circuit](#)
- S-R latch

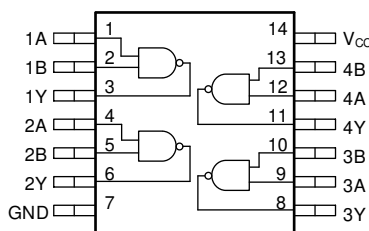
### 3 Description

This device contains four independent 2-input NAND Gates. Each gate performs the Boolean function  $Y = \overline{A \bullet B}$  in positive logic.

#### Device Information

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)
SN74HC00D	SOIC (14)	8.70 mm × 3.90 mm
SN74HC00DB	SSOP (14)	6.50 mm × 5.30 mm
SN74HC00N	PDIP (14)	19.30 mm × 6.40 mm
SN74HC00NS	SO (14)	10.20 mm × 5.30 mm
SN74HC00PW	TSSOP (14)	5.00 mm × 4.40 mm
SN54HC00FK	LCCC (20)	8.90 mm × 8.90 mm
SN54HC00J	CDIP (14)	21.30 mm × 7.60 mm
SN54HC00W	CFP (14)	9.20 mm × 6.29 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



**Device Functional Pinout**



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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision G (January 2021) to Revision H (August 2021)</b>	<b>Page</b>
• Increased D and PW package thermal values.....	5

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<b>Changes from Revision F (July 2016) to Revision G (January 2021)</b>	<b>Page</b>
• Updated to new data sheet format.....	1
• Updated D and PW package thermals to new standards.....	5

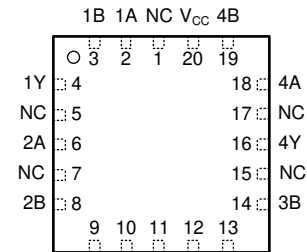
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<b>Changes from Revision E (August 2003) to Revision F (July 2016)</b>	<b>Page</b>
• Added <i>Applications</i> section, <i>Device Information</i> table, <i>ESD Ratings</i> table, <i>Typical Characteristics</i> section, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section.....	1
• Added Military Disclaimer to Features list.....	1
• Removed Ordering Information table; see POA at the end of data sheet.....	1
• Changed values in the Thermal Information table to align with JEDEC standards.....	5
• Deleted <i>Operating Characteristics</i> table; moved Cpd row to <i>Electrical Characteristics</i> .....	5

## 5 Pin Configuration and Functions



**D, DB, N, NS, PW, J, or W Package**  
**14-Pin SOIC, SSOP, PDIP, SO, TSSOP, CDIP, or CFP**  
**Top View**



**FK Package**  
**20-Pin LCCC**  
**Top View**

**Table 5-1. Pin Functions**

NAME	PIN		I/O	DESCRIPTION
	D, DB, N, NS, PW, J, or W	FK		
1A	1	2	Input	Channel 1, Input A
1B	2	3	Input	Channel 1, Input B
1Y	3	4	Output	Channel 1, Output Y
2A	4	6	Input	Channel 2, Input A
2B	5	8	Input	Channel 2, Input B
2Y	6	9	Output	Channel 2, Output Y
3A	9	13	Input	Channel 3, Input A
3B	10	14	Input	Channel 3, Input B
3Y	8	12	Output	Channel 3, Output Y
4A	12	18	Input	Channel 4, Input A
4B	13	19	Input	Channel 4, Input B
4Y	11	16	Output	Channel 4, Output Y
GND	7	10	—	Ground
NC		1, 5, 7, 11, 15, 17	—	Not internally connected
V <sub>CC</sub>	14	20	—	Positive Supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V		±20 mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V		±20 mA
I <sub>O</sub>	Continuous output current	V <sub>O</sub> = 0 to V <sub>CC</sub>		±25 mA
	Continuous current through V <sub>CC</sub> or GND			±50 mA
T <sub>J</sub>	Junction temperature <sup>(3)</sup>			150 °C
T <sub>stg</sub>	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 <sup>(1)</sup>	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2	5	6	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 2 V	1.5		V
		V <sub>CC</sub> = 4.5 V	3.15		
		V <sub>CC</sub> = 6 V	4.2		
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 2 V		0.5	V
		V <sub>CC</sub> = 4.5 V		1.35	
		V <sub>CC</sub> = 6 V		1.8	
V <sub>I</sub>	Input voltage	0		V <sub>CC</sub>	V
V <sub>O</sub>	Output voltage	0		V <sub>CC</sub>	V
t <sub>t</sub>	Input transition rise and fall time	V <sub>CC</sub> = 2 V		1000	ns
		V <sub>CC</sub> = 4.5 V		500	
		V <sub>CC</sub> = 6 V		400	
T <sub>A</sub>	Operating free-air temperature	SN54HC00	-55	125	°C
		SN74HC00	-40	85	

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		SN74HC00					UNIT
		D (SOIC)	DB (SSOP)	N (PDIP)	NS (SOP)	PW (TSSOP)	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	133.6	108.3	57.5	91.0	151.7	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	89.0	60.3	45.1	48.8	79.4	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	89.5	55.7	37.3	49.8	94.7	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	45.5	25	30.3	18.4	25.2	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	89.1	55.2	37.2	49.5	94.1	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics - Commercial (74xx)

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup> <sup>(2)</sup>

PARAMETER		TEST CONDITIONS		V <sub>CC</sub>	Operating free-air temperature (T <sub>A</sub> )						UNIT	
					25°C			-40°C to 85°C				
					MIN	TYP	MAX	MIN	TYP	MAX		
V <sub>OH</sub>	High-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -20 μA	2 V	1.9	1.998		1.9			V	
				4.5 V	4.4	4.499		4.4				
				6 V	5.9	5.999		5.9				
			I <sub>OH</sub> = -4 mA	4.5 V	3.98	4.3		3.84				
				6 V	5.48	5.8		5.34				
V <sub>OL</sub>	Low-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 20 μA	2 V		0.002	0.1			0.1	V	
				4.5 V		0.001	0.1			0.1		
				6 V		0.001	0.1			0.1		
			I <sub>OL</sub> = 4 mA	4.5 V		0.17	0.26			0.33		
				6 V		0.15	0.26			0.33		
I <sub>I</sub>	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> or 0		6 V		±0.1	±100			±1000	μA	
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or 0	V <sub>I</sub> = V <sub>CC</sub> or 0	6 V						2	20	μA
C <sub>i</sub>	Input capacitance			2 V to 6 V			3	10			10	pF
C <sub>pd</sub>	Power dissipation capacitance per gate	No load		2 V to 6 V			20					pF

(1) V<sub>CC1</sub> is the V<sub>CC</sub> associated with the input port.

(2) V<sub>CC0</sub> is the V<sub>CC</sub> associated with the output port.

## 6.6 Electrical Characteristics - Military (54xx)

 over operating free-air temperature range (unless otherwise noted) <sup>(1) (2)</sup>

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	Operating free-air temperature (T <sub>A</sub> )						UNIT	
			25°C			-55°C to 125°C				
			MIN	TYP	MAX	MIN	TYP	MAX		
V <sub>OH</sub>	High-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -20 μA	2 V	1.9	1.998		1.9	V	
				4.5 V	4.4	4.499		4.4		
				6 V	5.9	5.999		5.9		
			I <sub>OH</sub> = -4 mA	4.5 V	3.98	4.3		3.7		
				6 V	5.48	5.8		5.2		
V <sub>OL</sub>	Low-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 20 μA	2 V		0.002	0.1		0.1	V
				4.5 V		0.001	0.1		0.1	
				6 V		0.001	0.1		0.1	
			I <sub>OL</sub> = 4 mA	4.5 V		0.17	0.26		0.4	
				6 V		0.15	0.26		0.4	
I <sub>I</sub>	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> or 0	6 V		±0.1	±100		±1000	nA	
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or 0	V <sub>I</sub> = V <sub>CC</sub> or 0	6 V			2		40	μA
C <sub>i</sub>	Input capacitance		2 V to 6 V		3	10			10	pF
C <sub>pd</sub>	Power dissipation capacitance per gate	No load	2 V to 6 V		20					pF

 (1) V<sub>CCI</sub> is the V<sub>CC</sub> associated with the input port.

 (2) V<sub>CCO</sub> is the V<sub>CC</sub> associated with the output port.

## 6.7 Switching Characteristics - Commercial (74xx)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM	TO	V <sub>CC</sub>	Operating free-air temperature (T <sub>A</sub> )						UNIT
				25°C			-40°C to 85°C			
				MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>pd</sub>	Propagation delay	A or B	Y	2 V	45	90			115	ns
				4.5 V	9	18			23	
				6 V	8	15			20	
t <sub>t</sub>	Transition-time		Y	2 V	38	75			95	ns
				4.5 V	8	15			19	
				6 V	6	13			16	

## 6.8 Switching Characteristics - Military (54xx)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM	TO	V <sub>CC</sub>	Operating free-air temperature (T <sub>A</sub> )						UNIT
				25°C			-55°C to 125°C			
				MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>pd</sub>	Propagation delay	A or B	Y	2 V	45	90			135	ns
				4.5 V	9	18			27	
				6 V	8	15			23	

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM	TO	V <sub>CC</sub>	Operating free-air temperature (T <sub>A</sub> )						UNIT
				25°C			-55°C to 125°C			
				MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>t</sub>		Y	2 V		38	75		110	ns	
			4.5 V		8	15		22		
			6 V		6	13		19		

### 6.9 Typical Characteristics

T<sub>A</sub> = 25°C

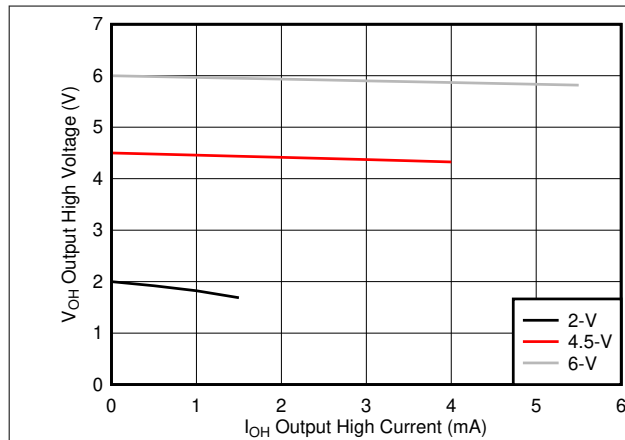


Figure 6-1. Typical Output Voltage in the High State (V<sub>OH</sub>)

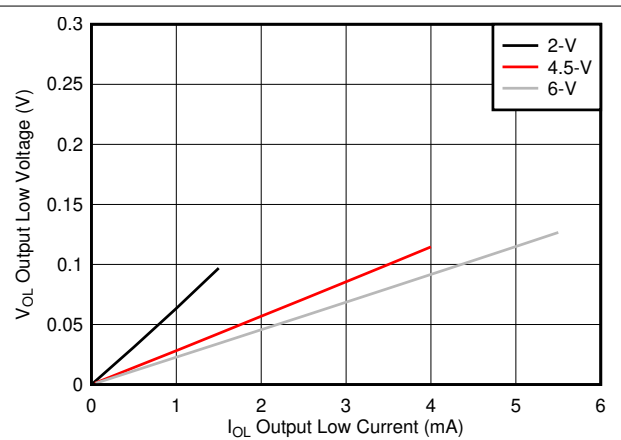


Figure 6-2. Typical Output Voltage in the Low State (V<sub>OL</sub>)

## 7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_t < 6 \text{ ns}$ .

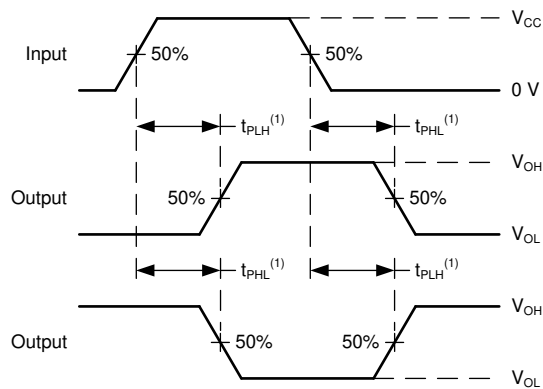
For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



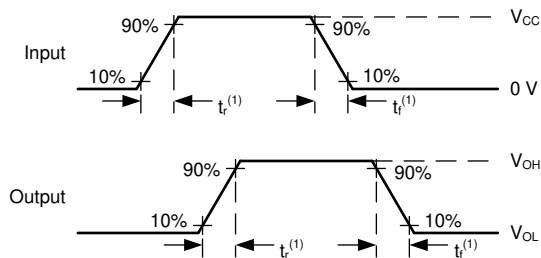
(1)  $C_L$  includes probe and test-fixture capacitance.

**Figure 7-1. Load Circuit for Push-Pull Outputs**



(1) The greater between  $t_{pLH}$  and  $t_{pHL}$  is the same as  $t_{pd}$ .

**Figure 7-2. Voltage Waveforms Propagation Delays**



(1) The greater between  $t_r$  and  $t_f$  is the same as  $t_t$ .

**Figure 7-3. Voltage Waveforms, Input and Output Transition Times**



## 8 Detailed Description

### 8.1 Overview

This device contains four independent 2-input NAND gates. Each gate performs the Boolean function  $Y = \overline{A \bullet B}$  in positive logic.

### 8.2 Functional Block Diagram



### 8.3 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

### 8.4 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ( $R = V \div I$ ).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in [Implications of Slow or Floating CMOS Inputs](#).

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors, however a 10-k $\Omega$  resistor is recommended and will typically meet all requirements.

### 8.5 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Electrical Placement of Clamping Diodes for Each Input and Output](#).

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

### 8.6 Device Functional Modes

Table 8-1. Function Table

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

## 9 Application and Implementation

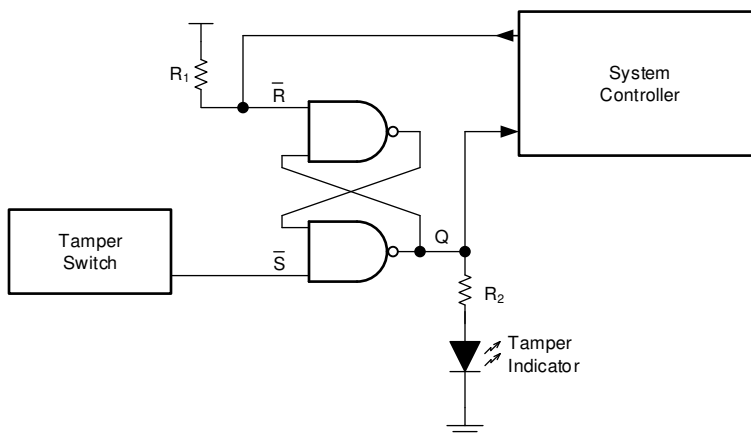
### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

In this application, the SN74HC00 is used to create an active-low SR latch. The two additional gates can be used for a second active-low SR latch, individually used for their logic function, or the inputs can be grounded and both channels left unused. This device is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs LOW, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a LOW signal to the R input which returns the Q output back to LOW.

### 9.2 Typical Application



**Figure 9-1. Typical Application Diagram**

#### 9.2.1 Design Requirements

##### 9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HC00 plus the maximum static supply current,  $I_{CC}$ , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HC00 plus the maximum supply current,  $I_{CC}$ , listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HC00 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74HC00 can drive a load with total resistance described by  $R_L \geq V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

#### CAUTION

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 9.2.1.2 Input Considerations

Input signals must cross  $V_{IL(max)}$  to be considered a logic LOW, and  $V_{IH(min)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HC00, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74HC00 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

#### 9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to  $V_{CC}$  or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

### 9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from  $V_{CC}$  to GND. The capacitor needs to be placed physically close to the device and electrically close to both the  $V_{CC}$  and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is  $\leq 50$  pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HC00 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ . This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in  $M\Omega$ ; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

### 9.2.3 Application Curve



**Figure 9-2. Application Timing Diagram**

## 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu\text{F}$  capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu\text{F}$  and 1- $\mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

## 11 Layout

### 11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

### 11.2 Layout Example

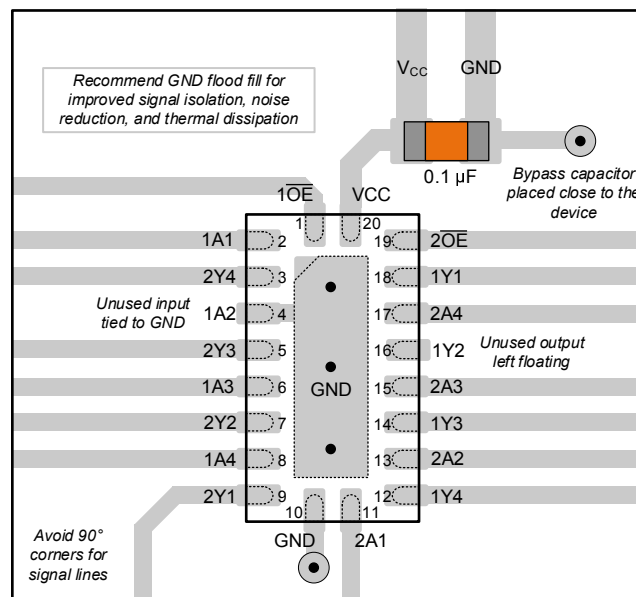


Figure 11-1. Example layout for the SN74HC00 in the RKS Package

## 12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 12.1 Documentation Support

### 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 12.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

### 12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8403701VCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8403701VC A SNV54HC00J	<a href="#">Samples</a>
5962-8403701VDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8403701VD A SNV54HC00W	<a href="#">Samples</a>
84037012A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	84037012A SNJ54HC 00FK	<a href="#">Samples</a>
8403701CA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8403701CA SNJ54HC00J	<a href="#">Samples</a>
8403701DA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8403701DA SNJ54HC00W	<a href="#">Samples</a>
JM38510/65001B2A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65001B2A	<a href="#">Samples</a>
JM38510/65001BCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65001BCA	<a href="#">Samples</a>
JM38510/65001BDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65001BDA	<a href="#">Samples</a>
M38510/65001B2A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65001B2A	<a href="#">Samples</a>
M38510/65001BCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65001BCA	<a href="#">Samples</a>
M38510/65001BDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65001BDA	<a href="#">Samples</a>
SN54HC00J	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	SN54HC00J	<a href="#">Samples</a>
SN74HC00D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DE4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>



Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HC00DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DTE4	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00DTG4	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU   SN	N / A for Pkg Type	-40 to 85	SN74HC00N	<a href="#">Samples</a>
SN74HC00NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC00N	<a href="#">Samples</a>
SN74HC00NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00PW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00PWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SN74HC00PWT	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC00	<a href="#">Samples</a>
SNJ54HC00FK	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	84037012A SNJ54HC 00FK	<a href="#">Samples</a>
SNJ54HC00J	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8403701CA SNJ54HC00J	<a href="#">Samples</a>
SNJ54HC00W	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8403701DA SNJ54HC00W	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of  $\leq 1000$ ppm threshold. Antimony trioxide based flame retardants must also meet the  $\leq 1000$ ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**OTHER QUALIFIED VERSIONS OF SN54HC00, SN54HC00-SP, SN74HC00 :**

- Catalog : [SN74HC00](#), [SN54HC00](#)
  
- Automotive : [SN74HC00-Q1](#), [SN74HC00-Q1](#)
  
- Military : [SN54HC00](#)
  
- Space : [SN54HC00-SP](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military - QML certified for Military and Defense Applications
- Space - Radiation tolerant, ceramic packaging and qualified for use in Space-based application

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC00DBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74HC00DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC00DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HC00DR	SOIC	D	14	2500	330.0	16.8	6.5	9.5	2.1	8.0	16.0	Q1
SN74HC00DRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC00DRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC00DT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC00NSR	SO	NS	14	2000	330.0	16.4	8.45	10.55	2.5	12.0	16.2	Q1
SN74HC00PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HC00PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HC00PWR	TSSOP	PW	14	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1
SN74HC00PWRG4	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HC00PWT	TSSOP	PW	14	250	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC00DBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74HC00DR	SOIC	D	14	2500	367.0	367.0	38.0
SN74HC00DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HC00DR	SOIC	D	14	2500	364.0	364.0	27.0
SN74HC00DRG4	SOIC	D	14	2500	340.5	336.1	32.0
SN74HC00DRG4	SOIC	D	14	2500	367.0	367.0	38.0
SN74HC00DT	SOIC	D	14	250	210.0	185.0	35.0
SN74HC00NSR	SO	NS	14	2000	356.0	356.0	35.0
SN74HC00PWR	TSSOP	PW	14	2000	364.0	364.0	27.0
SN74HC00PWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74HC00PWR	TSSOP	PW	14	2000	366.0	364.0	50.0
SN74HC00PWRG4	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74HC00PWT	TSSOP	PW	14	250	356.0	356.0	35.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-8403701VDA	W	CFP	14	1	506.98	26.16	6220	NA
84037012A	FK	LCCC	20	1	506.98	12.06	2030	NA
JM38510/65001B2A	FK	LCCC	20	1	506.98	12.06	2030	NA
M38510/65001B2A	FK	LCCC	20	1	506.98	12.06	2030	NA
SN74HC00D	D	SOIC	14	50	507	8	3940	4.32
SN74HC00D	D	SOIC	14	50	506.6	8	3940	4.32
SN74HC00DE4	D	SOIC	14	50	506.6	8	3940	4.32
SN74HC00DE4	D	SOIC	14	50	507	8	3940	4.32
SN74HC00DG4	D	SOIC	14	50	507	8	3940	4.32
SN74HC00DG4	D	SOIC	14	50	506.6	8	3940	4.32
SN74HC00N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC00N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC00N	N	PDIP	14	25	506.1	9	600	5.4
SN74HC00NE4	N	PDIP	14	25	506.1	9	600	5.4
SN74HC00NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC00NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC00PW	PW	TSSOP	14	90	530	10.2	3600	3.5
SNJ54HC00FK	FK	LCCC	20	1	506.98	12.06	2030	NA

FK (S-CQCC-N\*\*)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



NO. OF TERMINALS **	A		B	
	MIN	MAX	MIN	MAX
20	0.342 (8,69)	0.358 (9,09)	0.307 (7,80)	0.358 (9,09)
28	0.442 (11,23)	0.458 (11,63)	0.406 (10,31)	0.458 (11,63)
44	0.640 (16,26)	0.660 (16,76)	0.495 (12,58)	0.560 (14,22)
52	0.740 (18,78)	0.761 (19,32)	0.495 (12,58)	0.560 (14,22)
68	0.938 (23,83)	0.962 (24,43)	0.850 (21,6)	0.858 (21,8)
84	1.141 (28,99)	1.165 (29,59)	1.047 (26,6)	1.063 (27,0)



4040140/D 01/11

- NOTES:
- All linear dimensions are in inches (millimeters).
  - This drawing is subject to change without notice.
  - This package can be hermetically sealed with a metal lid.
  - Falls within JEDEC MS-004

# MECHANICAL DATA

NS (R-PDSO-G\*\*)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - C. This package can be hermetically sealed with a ceramic lid using glass frit.
  - D. Index point is provided on cap for terminal identification only.
  - E. Falls within MIL STD 1835 GDFP1-F14

J 14

**GENERIC PACKAGE VIEW**  
**CDIP - 5.08 mm max height**  
CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4040083-5/G

J0014A



# PACKAGE OUTLINE

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



4214771/A 05/2017

NOTES:

1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.

# EXAMPLE BOARD LAYOUT

J0014A

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



LAND PATTERN EXAMPLE  
NON-SOLDER MASK DEFINED  
SCALE: 5X



4214771/A 05/2017

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - $\triangle C$  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  - $\triangle D$  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

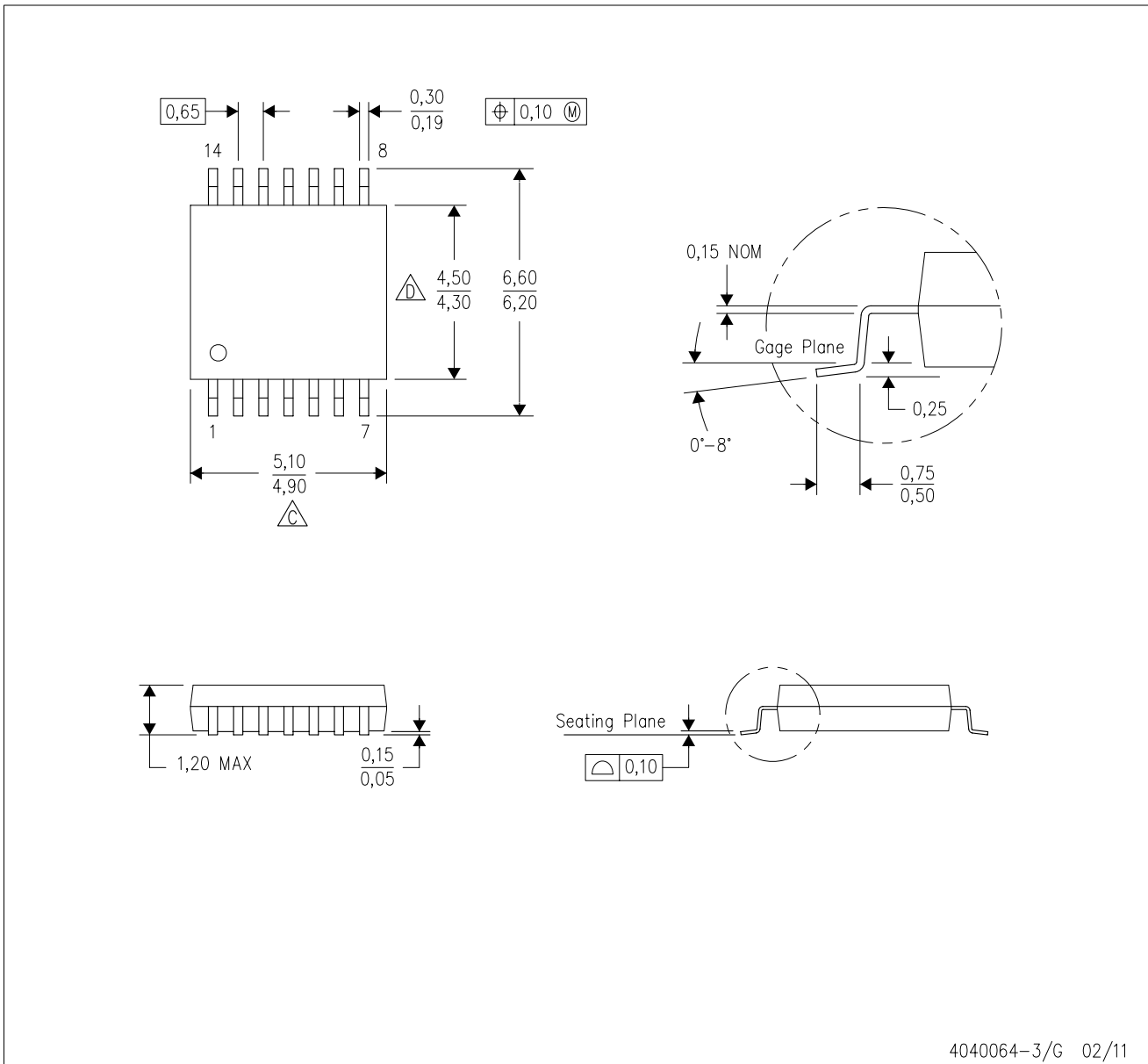
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4040064-3/G 02/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
  -  Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
  - E. Falls within JEDEC MO-153

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4211284-2/G 08/15

- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - (C) Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
  - (D) The 20 pin end lead shoulder width is a vendor option, either half or full width.

DB (R-PDSO-G\*\*)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.  
 B. This drawing is subject to change without notice.  
 C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.  
 D. Falls within JEDEC MO-150

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